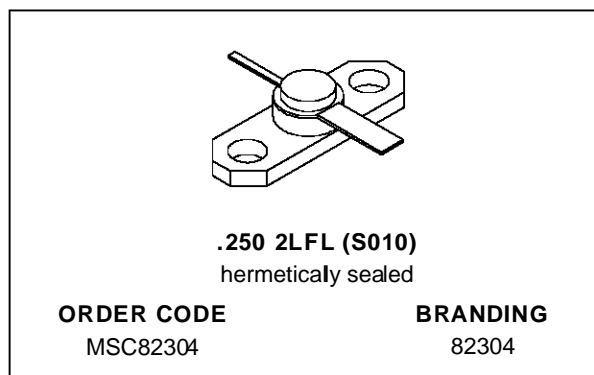


## RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

PRELIMINARY DATA

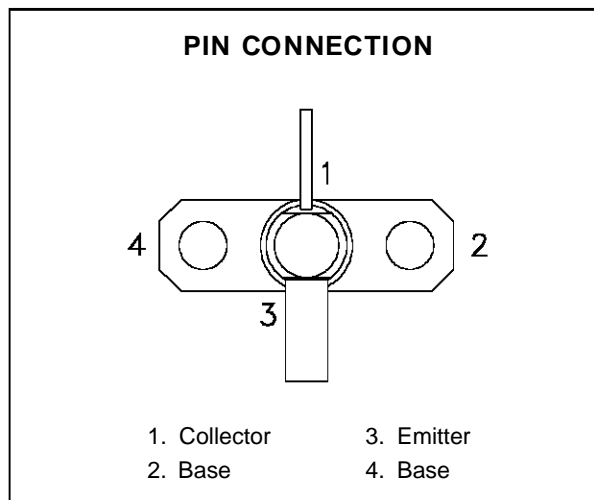
- REFRACTORY/GOLD METALLIZATION
- VSWR CAPABILITY 20:1 @ RATED CONDITIONS
- HERMETIC STRIPAC® PACKAGE
- P<sub>OUT</sub> = 3.8 W MIN. WITH 10.0 dB GAIN



### DESCRIPTION

The MSC82304 is a common base hermetically sealed silicon NPN microwave power transistor utilizing a rugged overlay die geometry. This device is capable of withstanding 20:1 load VSWR at any phase angle under rated conditions.

The MSC82304 was designed for Class C Amplifier/Oscillator applications in the 1.5 - 2.3 GHz frequency range.



### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

| Symbol            | Parameter                                  | Value        | Unit |
|-------------------|--|--------------|------|
| P <sub>DISS</sub> | Power Dissipation* (T <sub>c</sub> ≤ 50°C) | 11.5         | W    |
| I <sub>c</sub>    | Device Current*                            | 600          | mA   |
| V <sub>CC</sub>   | Collector-Supply Voltage*                  | 26           | V    |
| T <sub>J</sub>    | Junction Temperature                       | 200          | °C   |
| T <sub>STG</sub>  | Storage Temperature                        | - 65 to +200 | °C   |

### THERMAL DATA

|                      |                                   |    |      |
|----------------------|-----------------------------------|----|------|
| R <sub>TH(j-c)</sub> | Junction-Case Thermal Resistance* | 13 | °C/W |
|----------------------|-----------------------------------|----|------|

\*Applies only to rated RF amplifier operation

## MSC82304

### ELECTRICAL SPECIFICATIONS ( $T_{\text{case}} = 25^{\circ}\text{C}$ )

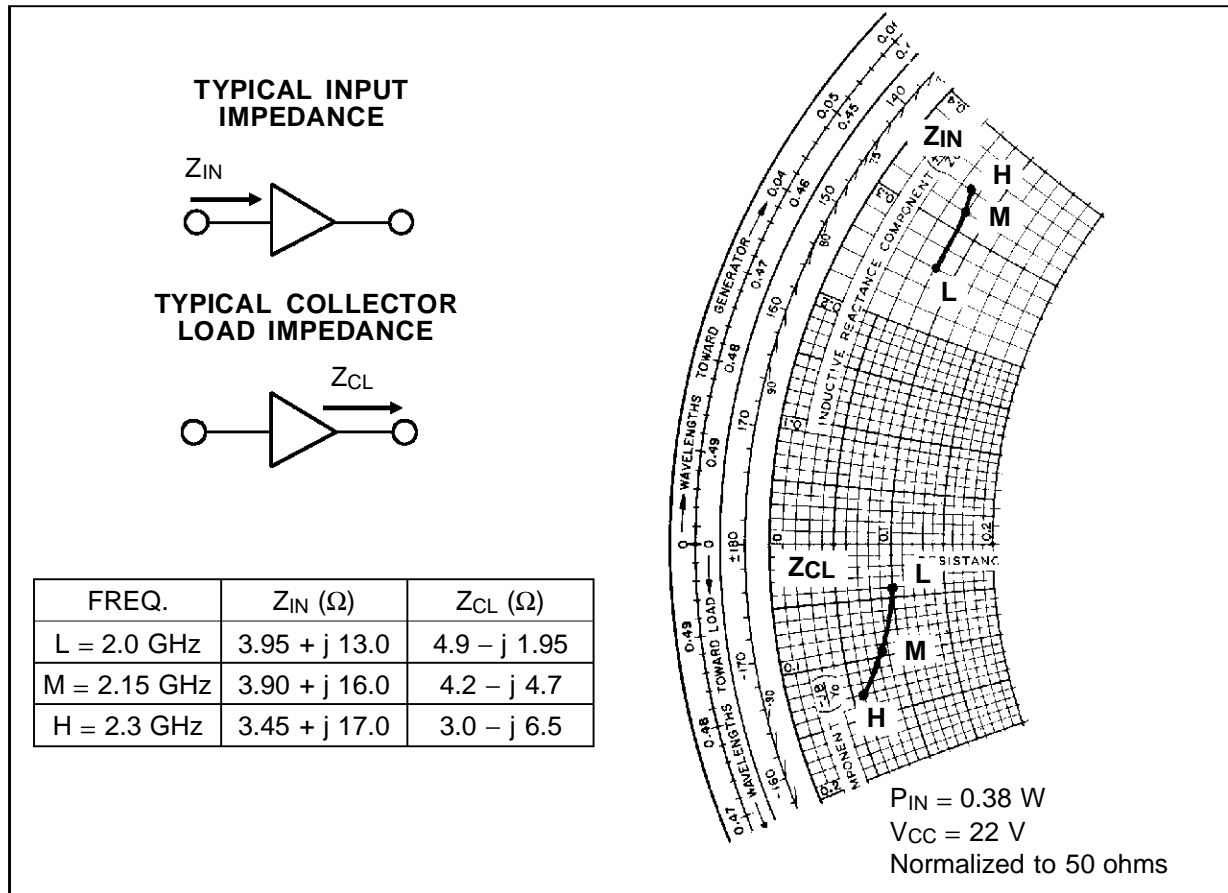
#### STATIC

| Symbol            | Test Conditions              |                               |     | Value |      |      | Unit |
|-------------------|------------------------------|-------------------------------|-----|-------|------|------|------|
|                   |                              |                               |     | Min.  | Typ. | Max. |      |
| $BV_{\text{CBO}}$ | $I_{\text{C}} = 1\text{mA}$  | $I_{\text{E}} = 0\text{mA}$   | 44  | —     | —    | V    |      |
| $BV_{\text{EBO}}$ | $I_{\text{E}} = 1\text{mA}$  | $I_{\text{C}} = 0\text{mA}$   | 3.5 | —     | —    | V    |      |
| $BV_{\text{CER}}$ | $I_{\text{C}} = 5\text{mA}$  | $R_{\text{BE}} = 10\Omega$    | 44  | —     | —    | V    |      |
| $I_{\text{CBO}}$  | $V_{\text{CB}} = 22\text{V}$ |                               | —   | —     | 0.5  | mA   |      |
| $h_{\text{FE}}$   | $V_{\text{CE}} = 5\text{V}$  | $I_{\text{C}} = 250\text{mA}$ | 30  | —     | 300  | —    |      |

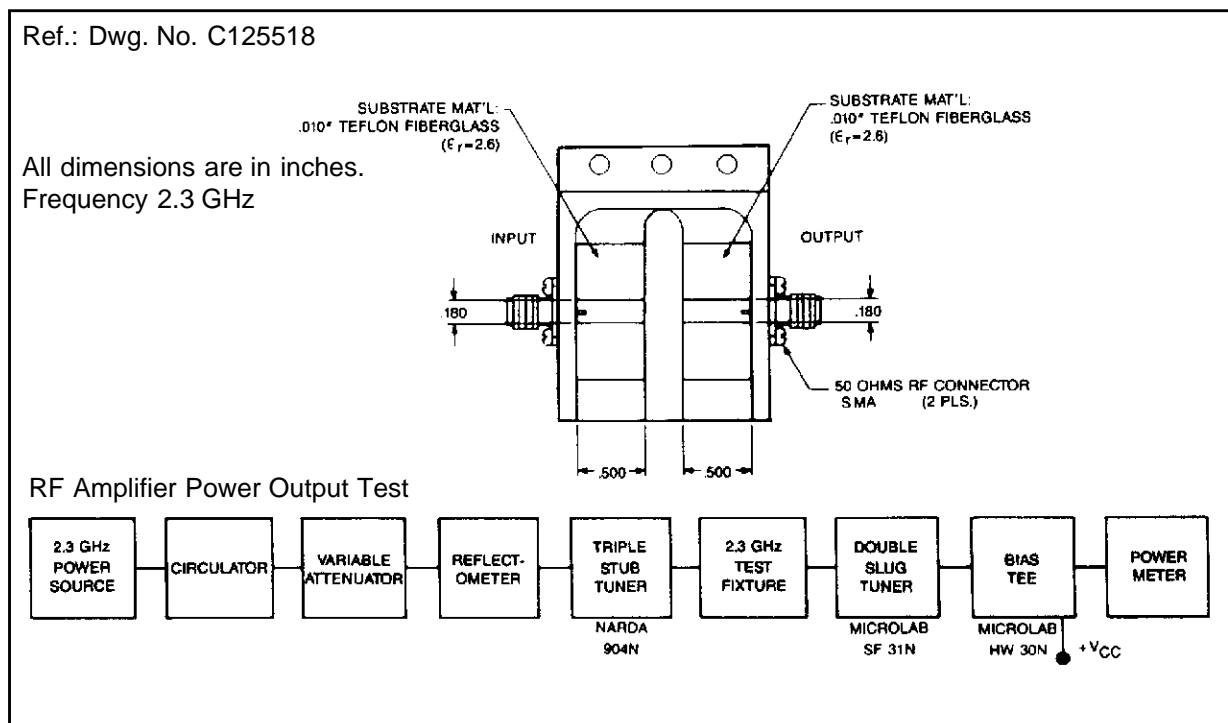
#### DYNAMIC

| Symbol            | Test Conditions      |                                 |                               | Value |      |      | Unit |
|-------------------|----------------------|---------------------------------|-------------------------------|-------|------|------|------|
|                   |                      |                                 |                               | Min.  | Typ. | Max. |      |
| $P_{\text{OUT}}$  | $f = 2.3\text{ GHz}$ | $P_{\text{IN}} = 0.38\text{ W}$ | $V_{\text{CC}} = 22\text{ V}$ | 3.8   | —    | —    | W    |
| $\eta_{\text{C}}$ | $f = 2.3\text{ GHz}$ | $P_{\text{IN}} = 0.38\text{ W}$ | $V_{\text{CC}} = 22\text{ V}$ | 40    | —    | —    | %    |
| $G_{\text{P}}$    | $f = 2.3\text{ GHz}$ | $P_{\text{IN}} = 0.38\text{ W}$ | $V_{\text{CC}} = 22\text{ V}$ | 10.0  | —    | —    | dB   |
| $C_{\text{OB}}$   | $f = 1\text{ MHz}$   | $V_{\text{CB}} = 22\text{ V}$   |                               | —     | —    | 5.0  | pF   |

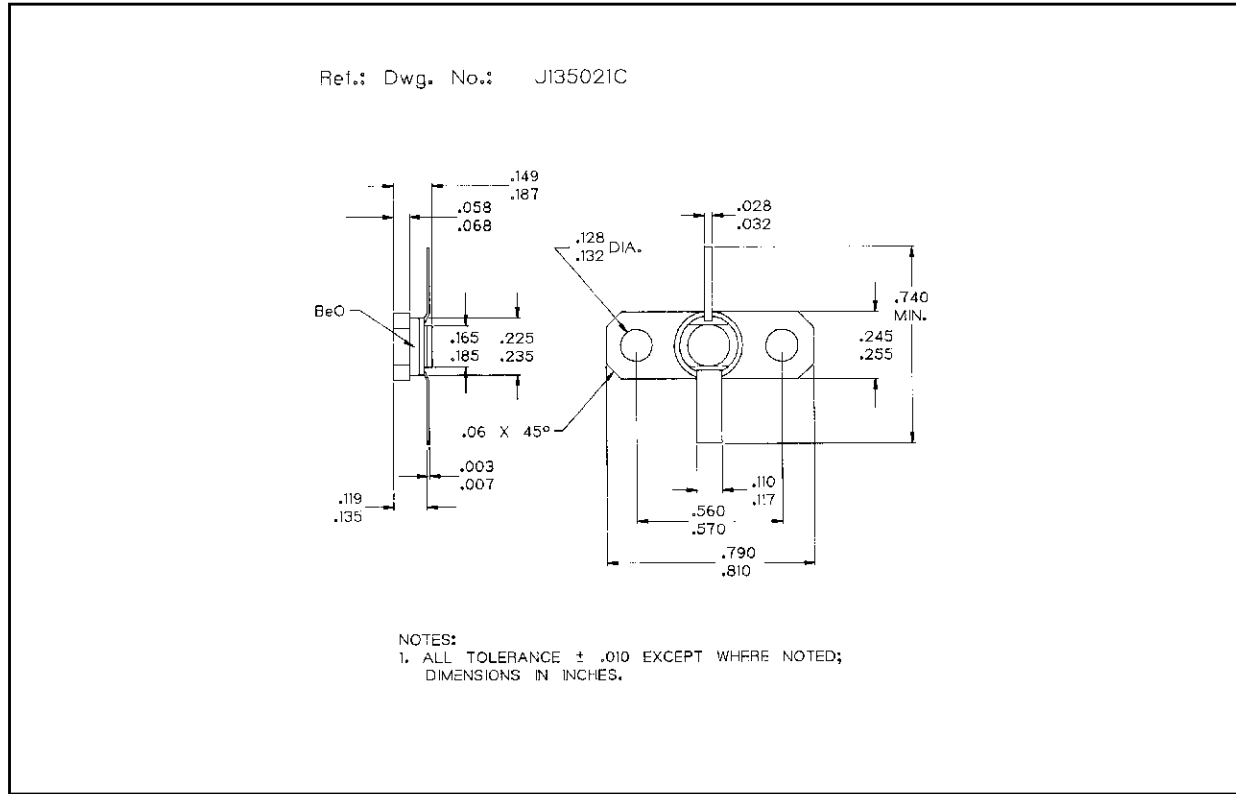
IMPEDANCE DATA



TEST CIRCUIT



PACKAGE MECHANICAL DATA



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